

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|--------|------------------------------|-------------------------------------------------------------------|------------------|---------|------------------|
| L1 | 18004 | pzt | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:47 |
| L3 | 64953 | metallization | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:47 |
| L4 | 5427 | selective adj deposition | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:48 |
| L5 | 1248 | 3 and 4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:48 |
| L6 | 55522 | etchant | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:48 |
| L7 | 133156 | silicon adj oxide | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:48 |
| L8 | 116 | 5 and 6 and 7 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 15:14 |
| L10 | 13600 | contact adj (window or mask) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:53 |

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| L11 | 50 | 1 and 10 and 6 and 7 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:56 |
| L12 | 538570 | contact adj window or mask | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:53 |
| L13 | 584 | 10 and 12 and 6 and 7 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:54 |
| L14 | 2 | "5593914".pn. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:55 |
| L15 | 4493 | 1 and 12 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:56 |
| L16 | 732 | 15 and 6 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:56 |
| L17 | 366 | 16 and 7 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:58 |
| L18 | 47354 | lower adj electrode | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 14:58 |

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| L19 | 30 | (titanium and upper adj electrode and lower adj electrode and contact adj window) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 15:15 |
| L20 | 3 | (titanium and upper adj electrode and lower adj electrode and contact adj window).clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/12 15:15 |
| L21 | 3 | ("5352623" "5554559" "5750419").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/12/12 16:07 |
| S1 | 3283 | ammonium adj fluoride and hydrochloric adj acid | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 16:21 |
| S2 | 714 | etching and S1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 09:16 |
| S3 | 468 | semiconductor and S2 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 09:25 |
| S4 | 19297 | silicon adj oxide adj layer and "4" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 09:25 |
| S5 | 19297 | silicon adj oxide adj layer and S4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 09:25 |
| S6 | 37 | silicon adj oxide adj layer and S3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 10:38 |

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| S7 | 2 | ("4759823").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/23 10:35 |
| S8 | 2 | ("5350448").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/23 10:35 |
| S9 | 2 | ("5445979").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/23 10:35 |
| S10 | 2 | ("3777227").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/23 10:35 |
| S11 | 2 | ("5256247").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/23 10:36 |
| S12 | 2 | ("5402807").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/23 10:36 |
| S13 | 2 | ("5828129").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/23 10:36 |
| S14 | 2 | ("5587046").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/23 10:36 |

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| S15 | 3 | ("3911613").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/23 10:37 |
| S16 | 3283 | ammonium adj fluoride and hydrochloric adj acid | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 10:38 |
| S17 | 714 | etching and S16 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 10:38 |
| S18 | 468 | semiconductor and S17 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 10:38 |
| S19 | 37 | silicon adj oxide adj layer and S18 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 10:38 |
| S20 | 34 | S19 and device | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 10:40 |
| S21 | 500 | device and etching and ammonium adj fluoride and hydrochloric adj acid | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 10:41 |
| S22 | 34 | S20 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 10:41 |

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| S23 | 34 | S20 and semiconductor | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 10:57 |
| S24 | 1005 | device and titanium adj layer and silicon adj layer and etching | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 11:01 |
| S25 | 37162 | S24 and ammonium fluoride and hydrochloric adj acid | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 10:59 |
| S26 | 3 | S24 and ammonium adj fluoride and hydrochloric adj acid | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 10:59 |
| S27 | 3283 | ammonium adj fluoride and hydrochloric adj acid | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 11:01 |
| S28 | 300 | S27 and semiconductor adj device | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 11:02 |
| S29 | 268 | S28 and etching | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 11:04 |
| S30 | 268 | S29 and device | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 11:05 |

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| S31 | 1810896 | su "391613" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 11:06 |
| S32 | 3 | "391613".pn. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 11:06 |
| S33 | 0 | silicon adj oxide adj layer and titan adj layer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 11:53 |
| S34 | 5669 | silicon adj oxide and titanate | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 13:31 |
| S35 | 1875 | "2" and (batio or srtio or basrtio) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 12:50 |
| S36 | 1875 | S35 and (batio or srtio or basrtio) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 12:50 |
| S37 | 3 | "6620738" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 12:50 |
| S38 | 8 | ("3777227" "4759823" "5256247" "5350448" "5402807" "5445979" "5587046" "5828129").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/08/23 12:50 |
| S39 | 331 | pzt and silicon adj oxide adj layer and titanate | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 12:51 |

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| S40 | 869 | silicon adj oxide adj layer and titanate | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 12:51 |
| S41 | 2 | silicon adj oxide adj layer and titanante near3 layer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 12:53 |
| S43 | 2 | "6291319".pn. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 12:53 |
| S44 | 9 | ("5208182" "5225031" "5393352" "5450812" "5482003" "5514484" "5830270" "5907792" "6224669").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/08/23 12:53 |
| S45 | 3733906 | etched adj silicon layer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 13:31 |
| S46 | 230 | etched adj silicon adj layer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 13:32 |
| S47 | 3 | etched adj titanium adj layer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 13:33 |
| S48 | 9 | titanium adj layer adj etching | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 13:34 |
| S49 | 0 | (batio3 or srtio3) adj layer adj etching | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 13:34 |

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| S50 | 2 | "5326721".pn. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/23 14:30 |
| S51 | 206 | ishida-hidetoshi.in. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 08:18 |
| S52 | 26 | "6291319" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 08:18 |
| S55 | 8 | (("4759823") or ("5350448") or ("5445979") or ("5587046") or ("3777227") or ("5256247") or ("5402807") or ("5828129")).PN. | USPAT | OR | OFF | 2005/12/08 09:06 |
| S56 | 42024 | upper adj electrode | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:07 |
| S57 | 47336 | lower adj electrode | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:07 |
| S58 | 1 | S55 and S56 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:08 |
| S59 | 32253 | S56 and S57 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:08 |
| S60 | 486476 | etching | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:09 |

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| S61 | 11589 | S59 and S60 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:09 |
| S62 | 9135 | titanium adj layer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:09 |
| S63 | 325 | S61 and S62 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:57 |
| S64 | 2 | "5326721".pn. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:22 |
| S65 | 4219 | batio3 srtio3 basrtio3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:36 |
| S66 | 107 | S59 and S65 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:36 |
| S67 | 22463 | silicon adj oxide adj layer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:58 |
| S68 | 11 | S56 and S57 and S65 and S67 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 09:58 |

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| S69 | 133123 | silicon adj oxide | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 10:00 |
| S70 | 107 | S59 and S65 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:00 |
| S71 | 11 | S67 and S70 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 10:09 |
| S72 | 42024 | upper adj electrode | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:00 |
| S73 | 47336 | lower adj electrode | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:00 |
| S74 | 32253 | S72 and S73 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:00 |
| S75 | 486476 | etching | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:00 |
| S76 | 11589 | S74 and S75 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:00 |

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| S77 | 9135 | titanium adj layer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:00 |
| S78 | 325 | S76 and S77 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:01 |
| S79 | 22463 | silicon adj oxide adj layer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:01 |
| S80 | 134 | S72 and S73 and S77 and S79 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:35 |
| S81 | 4219 | batio3 srtio3 basrtio3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:16 |
| S82 | 11 | S72 and S73 and S79 and S81 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:16 |
| S83 | 107 | S72 and S73 and S81 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:17 |
| S84 | 2 | "5440157".pn. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:35 |